

## MOS FIELD EFFECT TRANSISTOR 2SJ557

### P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

#### **DESCRIPTION**

The 2SJ557 is a switching device which can be driven directly by a 4 V power source.

The 2SJ557 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

#### **FEATURES**

- Can be driven by a 4 V power source
- · Low on-state resistance

RDS(on)1 = 155 m $\Omega$  MAX. (VGS = -10 V, ID = -1.0 A)

RDS(on)2 = 255 m $\Omega$  MAX. (VGS = -4.5 V, ID = -1.0 A)

 $R_{DS(on)3} = 290 \text{ m}\Omega \text{ MAX. (Vgs} = -4.0 \text{ V, ID} = -1.0 \text{ A)}$ 

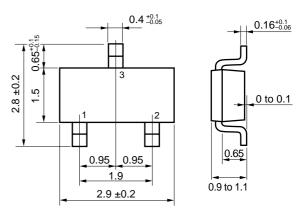
#### **ORDERING INFORMATION**

PART NUMBER	PACKAGE
2SJ557	3-pin Mini Mold (Thin Type)

#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

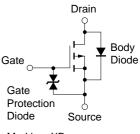
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	Vgss	-20 / +5	V
Drain Current (DC)	I <sub>D(DC)</sub>	±2.5	Α
Drain Current (pulse) Note1	ID(pulse)	±10	Α
Total Power Dissipation	P <sub>T1</sub>	0.2	W
Total Power Dissipation Note2	P <sub>T2</sub>	1.25	W
Channel Temperature	Tch	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

#### PACKAGE DRAWING (Unit: mm)



- 1 : Gate
- 2 : Source
- 3 : Drain

#### **EQUIVALENT CIRCUIT**



Marking: XB

- **Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1 %
  - **2.** Mounted on FR4 Board,  $t \le 5$  sec.

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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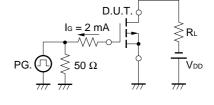
#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	Inss	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V			-10	μΑ
Gate Leakage Current	lgss	Vgs = ±16 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-1.0	-1.7	-2.5	V
Forward Transfer Admittance	<b>y</b> fs	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.5 A	1	2.5		S
Drain to Source On-state Resistance	RDS(on)1	Vgs = -10 V, ID = -1.0 A		114	155	mΩ
	RDS(on)2	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1.0 A		178	255	mΩ
	RDS(on)3	Vgs = -4.0 V, ID = -1.0 A		212	290	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = -10 V		312		pF
Output Capacitance	Coss	V <sub>G</sub> S = 0 V		117		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		56		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = −10 V		12		ns
Rise Time	tr	I <sub>D</sub> = -1.0 A		7		ns
Turn-off Delay Time	td(off)	$V_{GS(on)} = -10 \text{ V}$		133		ns
Fall Time	t <sub>f</sub>	$R_G = 10 \Omega$		85		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = -10 V		2.8		nC
Gate to Source Charge	Qgs	I <sub>D</sub> = -2.5 A		1.0		nC
Gate to Drain Charge	Q <sub>GD</sub>	V <sub>GS</sub> = -4.0 V		1.2		nC
Diode Forward Voltage	V <sub>F</sub> (S-D)	IF = 2.5 A, VGS = 0 V		0.84		V
Reverse Recovery Time	trr	IF = 2.5 A, VGS = 0 V		28		ns
Reverse Recovery Charge	Qrr	$di/dt = 50 A/\mu s$		7.8		nC

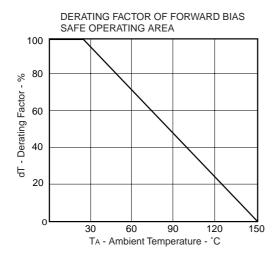
#### **TEST CIRCUIT 1 SWITCHING TIME**

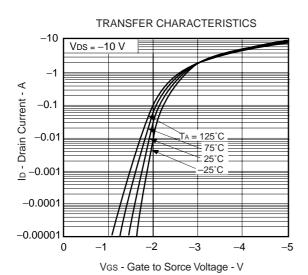
# PG. $\bigcap_{RG} RG = 10 \Omega$ $V_{GS} \bigvee_{Wave Form} V_{GS} \bigvee_{VGS(on)} 90 \%$ $V_{GS} \bigvee_{Wave Form} V_{GS(on)} \bigvee_{VGS(on)} 90 \%$ $V_{GS} \bigvee_{Wave Form} V_{GS(on)} \bigvee_{VGS(on)} 90 \%$ $V_{GS} \bigvee_{Wave Form} V_{GS(on)} \bigvee_{VGS(on)} 90 \%$ $V_{GS} \bigvee_{VGS(on)} V_{GS(on)} \bigvee_{VGS(on)} V_{GS(on$

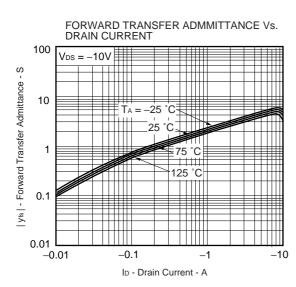
#### **TEST CIRCUIT 2 GATE CHARGE**

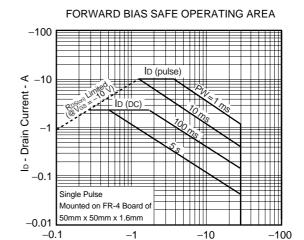


#### TYPICAL CHARACTERISTICS (TA = 25°C)

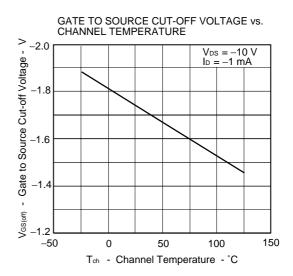




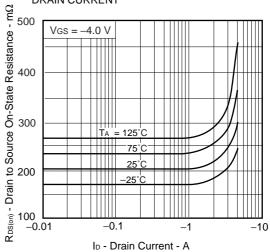




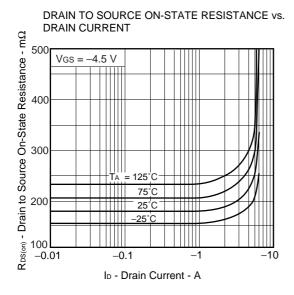
VDS - Drain to Source Voltage - V



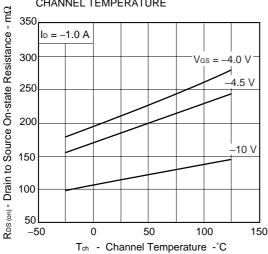
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



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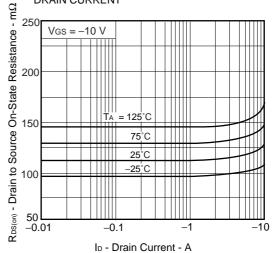


SOURCE VOLTAGE 1000 f = 1 MHzCiss, Coss, Crss - Capacitance - pF  $V_{GS} = 0V$ 100

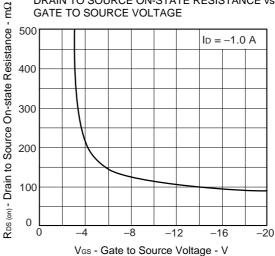
CAPACITANCE vs. DRAIN TO

-10 $V_{\text{DS}}$  - Drain to Source Voltage - V

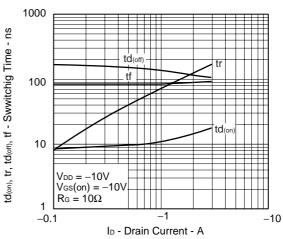
#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



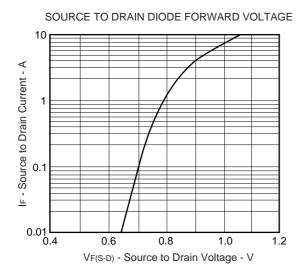
SWITCHING CHARACTERISTICS

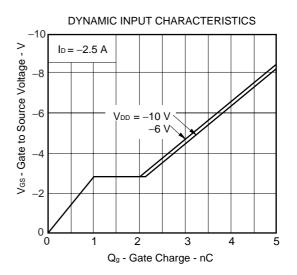


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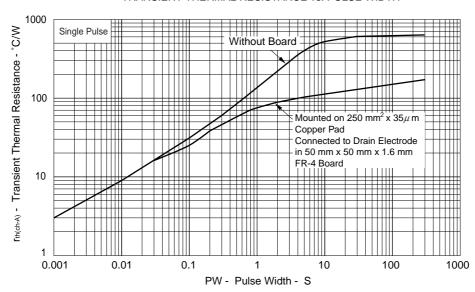
-1

-100





#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



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[MEMO]

**NEC** 2SJ557

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